

**Features**

- SiC MOSFET Technology
- High Speed Switching
- Reduction Of Heat Sink Requirements
- Essentially No Switching Losses
- Halogen Free. "Green" Device (Note 1)
- Lead Free Finish/RoHS Compliant("P" Suffix Designates RoHS Compliant. See Ordering Information) (Note2)

**Maximum Ratings**

- Operating Junction Temperature Range : -55°C to +175°C
- Storage Temperature Range: -55°C to +175°C
- Thermal Resistance Junction to Ambient,Max(Note 3): 62°C/W
- Thermal Resistance Junction to Case,Typ : 0.67°C/W

**Applications**

- Solar Inverters
- Uninterruptible Power Supply
- Photovoltaic Inverter
- Battery Chargers
- Motor Drives

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	$V_{DS}$	1200	V	
Gate-Source Voltage (Note 4)	$V_{GSmax}$	-10/+25	V	
Gate-Source Voltage	$V_{GSop}$	-5/+20	V	
Continuous Drain Current $V_{GS}=20V$	$I_D$	$T_c=25^\circ C$	33	A
		$T_c=110^\circ C$	24	
Pulsed Drain Current (Note 5)	$I_{DM}$	81	A	
Total Power Dissipation	$P_D$	$T_c=25^\circ C$	224	W
		$T_c=110^\circ C$	97	

Note1: Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

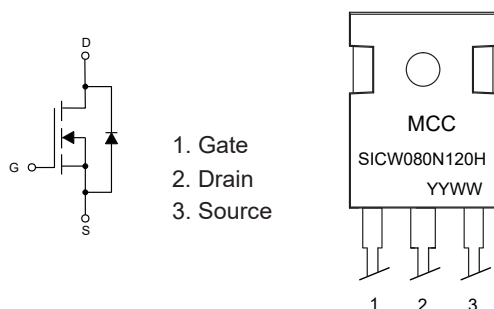
Note2: High Temperature Solder Exemptions Applied, see EU Directive Annex 7a.

Note3: Device in a still air environment with  $T_A=25^\circ C$ .

Note4: AC f > 1Hz, duty cycle < 1%

Note5: Pulse Test: Pulse Width Limited by  $T_{jmax}$ .

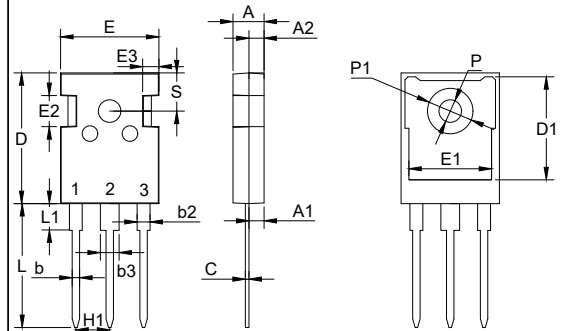
**Internal Structure and Marking Code**



Device Code: SICW080N120H  
Date Code: YYWW (Year & Week)

**SiC  
N-CHANNEL  
MOSFET**

**TO-247AB**



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.189	0.205	4.80	5.20	
A1	0.087	0.103	2.21	2.61	
A2	0.073	0.085	1.85	2.15	
b	0.039	0.055	1.00	1.40	
b2	0.075	0.087	1.91	2.21	
C	0.020	0.028	0.50	0.70	
D	0.815	0.839	20.70	21.30	
D1	0.640	0.663	16.25	16.85	
E	0.610	0.634	15.50	16.10	
E1	0.512	0.535	13.00	13.60	
E2	0.189	0.205	4.80	5.20	
E3	0.091	0.106	2.30	2.70	
L	0.772	0.796	19.62	20.22	
L1	-	0.177	-	4.50	
P	0.134	0.150	3.40	3.80	Φ
P1		0.287	-	7.30	Φ
S	0.242		6.15		TYP
H1	0.214		5.44		TYP
b3	0.110	0.126	2.80	3.20	

**Electrical Characteristics @ T<sub>j</sub>=25°C (Unless Otherwise Specified)**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
<b>Static Characteristics</b>							
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =100μA	1200			V	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =20V			250	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =1200V, V <sub>GS</sub> =0V			50	μA	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =20mA	2	3.0	4.5	V	
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =20V, I <sub>D</sub> =15A		80	110	mΩ	
		V <sub>GS</sub> =20V, I <sub>D</sub> =15A, T <sub>j</sub> =175°C		134		mΩ	
Internal Gate Resistance	R <sub>g</sub>	f=1MHz, V <sub>AC</sub> =25mV		0.75		Ω	
Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =9.8V, I <sub>D</sub> =15A		6.5		S	
<b>Dynamic Characteristics</b>							
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =800V, V <sub>GS</sub> =0V, f=1MHz, V <sub>AC</sub> =25mV		2644		pF	
Output Capacitance	C <sub>oss</sub>			85			
Reverse Transfer Capacitance	C <sub>rss</sub>			8			
Coss Stored Energy	E <sub>oss</sub>			33		μJ	
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =800V, V <sub>GS</sub> =-5/+20V, I <sub>D</sub> =20A		131		nC	
Gate-Source Charge	Q <sub>gs</sub>			53			
Gate-Drain Charge	Q <sub>gd</sub>			23			
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =800V, V <sub>GS</sub> =-5/+20V, R <sub>G</sub> =2.7Ω, I <sub>D</sub> =20A, R <sub>L</sub> =40Ω		28		ns	
Rise Time	t <sub>r</sub>			64			
Turn-Off Delay Time	t <sub>d(off)</sub>			60			
Fall Time	t <sub>f</sub>			26.4			
Turn-On switching energy	E <sub>on</sub>	V <sub>DD</sub> =800V, V <sub>GS</sub> =-5/+20V, R <sub>G</sub> =2.7Ω, I <sub>D</sub> =20A		22		μJ	
Turn-Off switching energy	E <sub>off</sub>			22			
<b>Diode Characteristics</b>							
Continuous Body Diode Current	I <sub>S</sub>	V <sub>GS</sub> =0V, T <sub>C</sub> =25°C		36		A	
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>SD</sub> =5A		3		V	
Reverse Recovery Time	t <sub>rr</sub>	V <sub>GS</sub> =0V, I <sub>SD</sub> =20A, V <sub>DS</sub> =400V, dI <sub>F</sub> /dt=300A/μs		50		ns	
Reverse Recovery Charge	Q <sub>rr</sub>				81		nC
Peak Reverse Recovery Current	I <sub>rrm</sub>				3.2		A

**Curve Characteristics** ( $T_J=25^\circ\text{C}$  unless otherwise specified)

Fig. 1 - Typical Output Characteristic ( $T_J=25^\circ\text{C}$ )

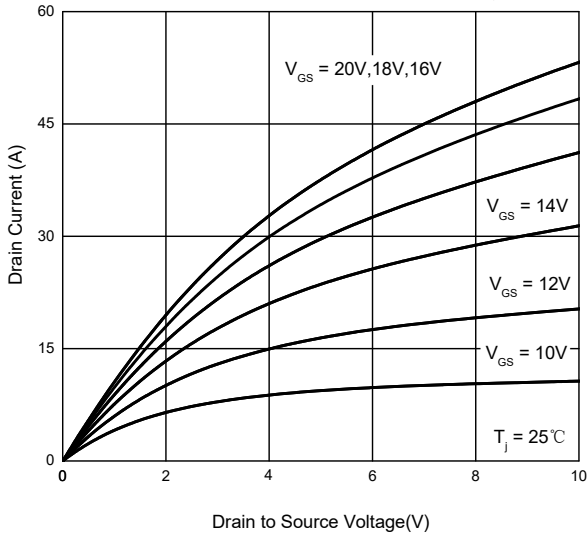


Fig. 2 - Typical Output Characteristic ( $T_J=175^\circ\text{C}$ )

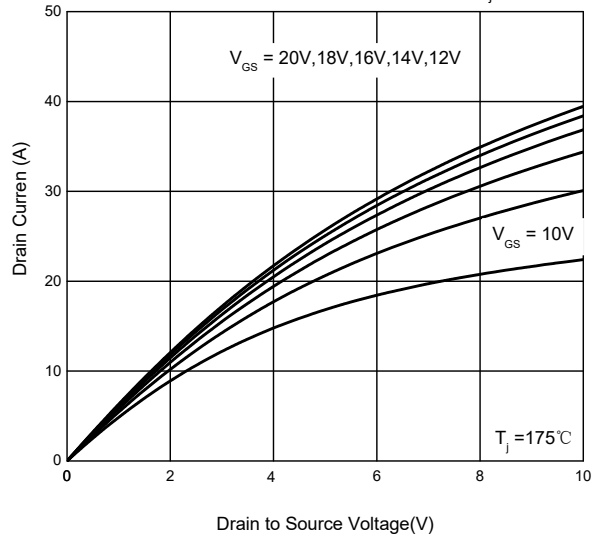


Fig. 3 - On-Resistance vs. Drain Current

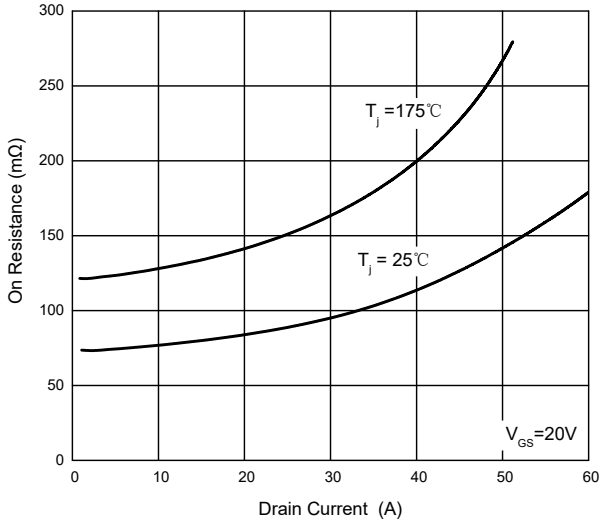


Fig. 4 - Typical Transfer Characteristic

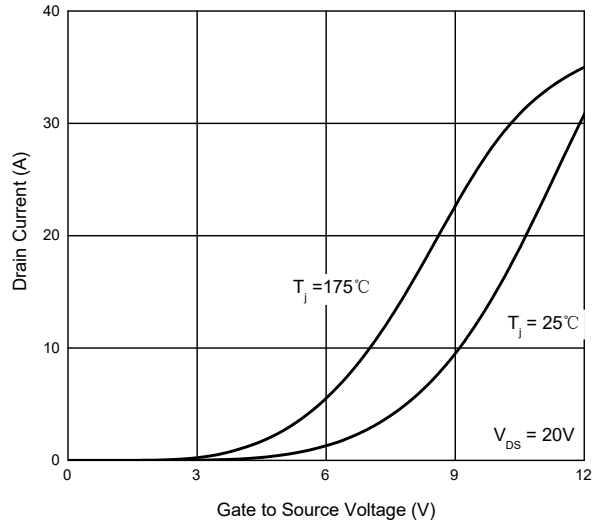


Fig. 5 - On-Resistance vs. Gate Voltage

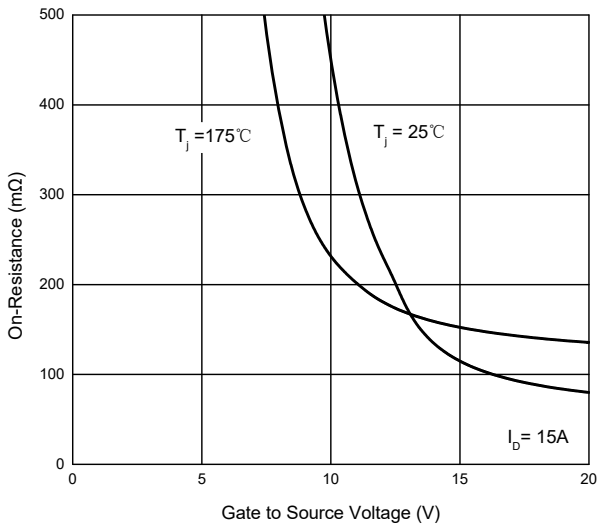
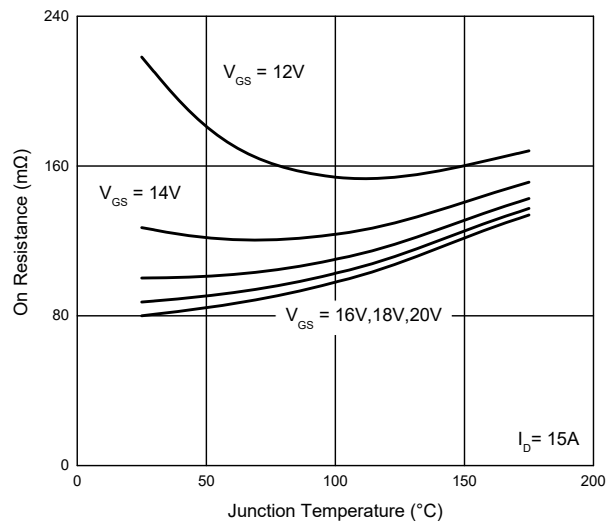
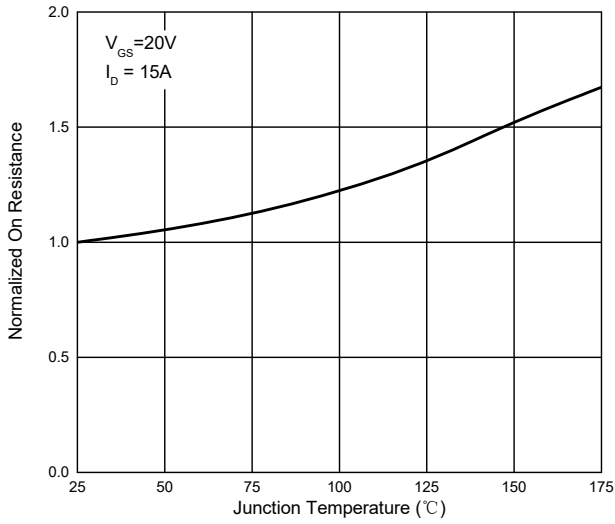


Fig. 6 - On-Resistance vs. Temperature

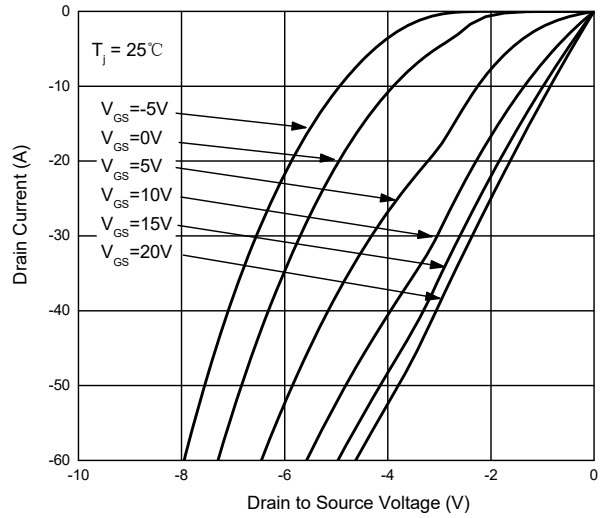


**Curve Characteristics** ( $T_J=25^\circ\text{C}$  unless otherwise specified)

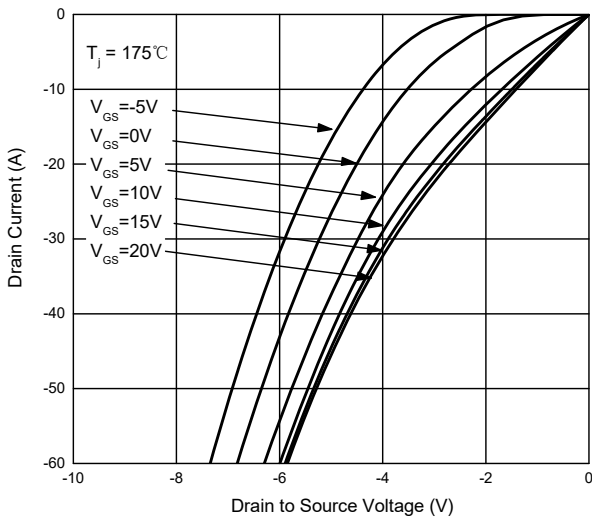
**Fig. 7 - Normalized On-Resistance vs. Temperature**



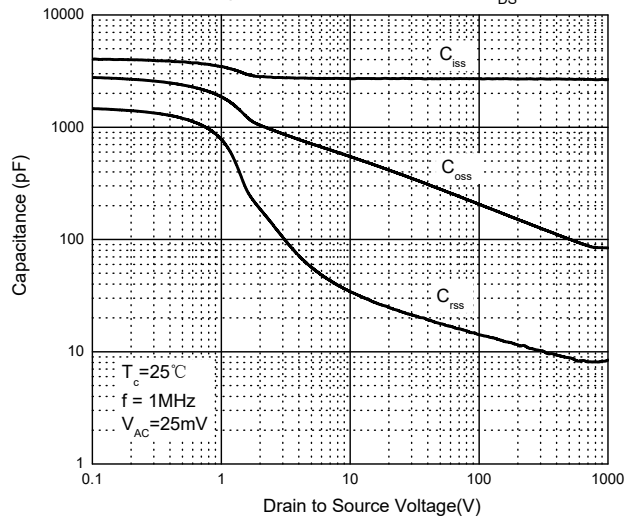
**Fig. 8 - Reverse Output Voltage**



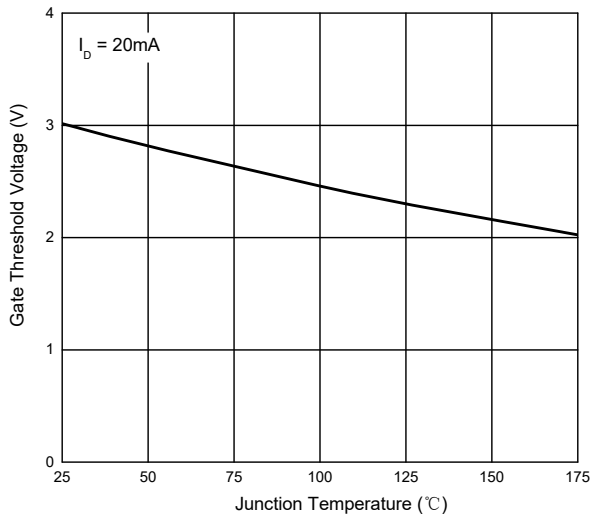
**Fig. 9 - Reverse Output Voltage**



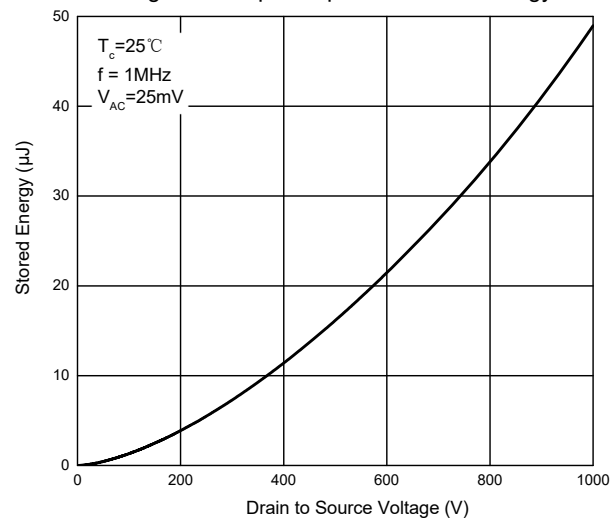
**Fig. 10 - Capacitances vs.  $V_{DS}$**



**Fig. 11 - Threshold Voltage vs. Temperature**

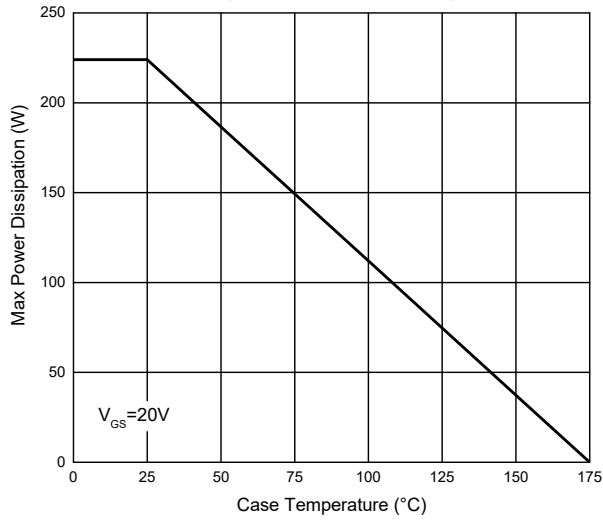


**Fig. 12 - Output Capacitor Stored Energy**

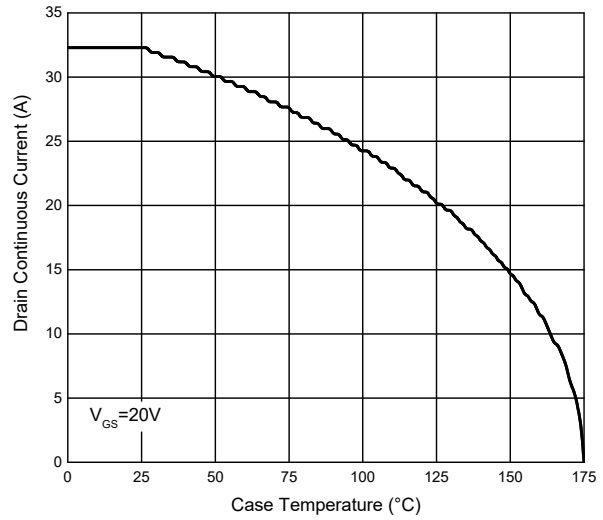


**Curve Characteristics** ( $T_J=25^\circ\text{C}$  unless otherwise specified)

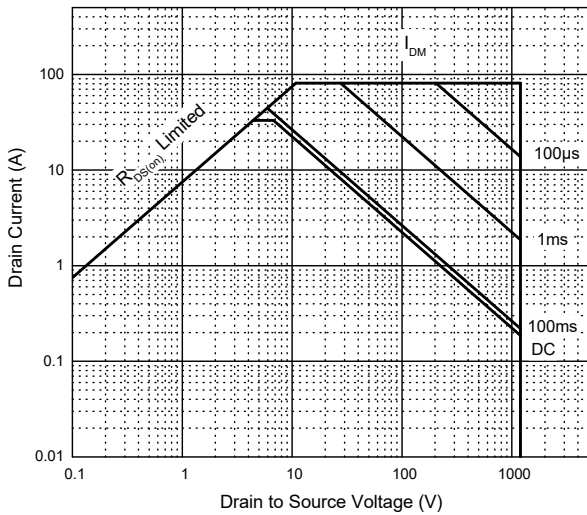
**Fig. 13 - Power Derating**



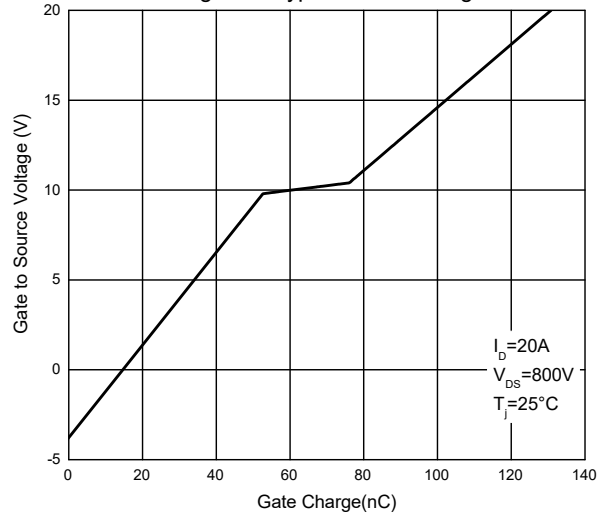
**Fig. 14 - Drain Current Derating**



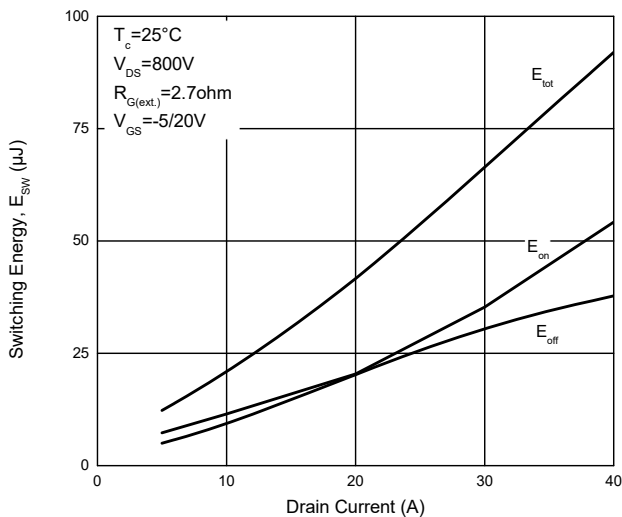
**Fig. 15 - Safe Operation Area**



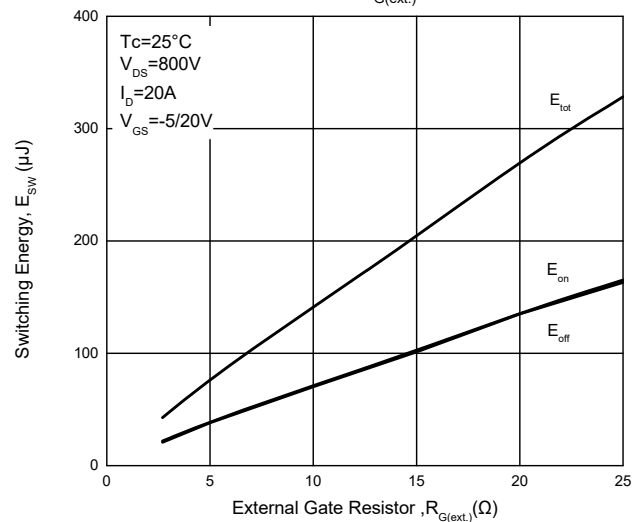
**Fig. 16 - Typical Gate Charge**



**Fig. 17 - Clamped Inductive Switching Energy vs. Drain Current**

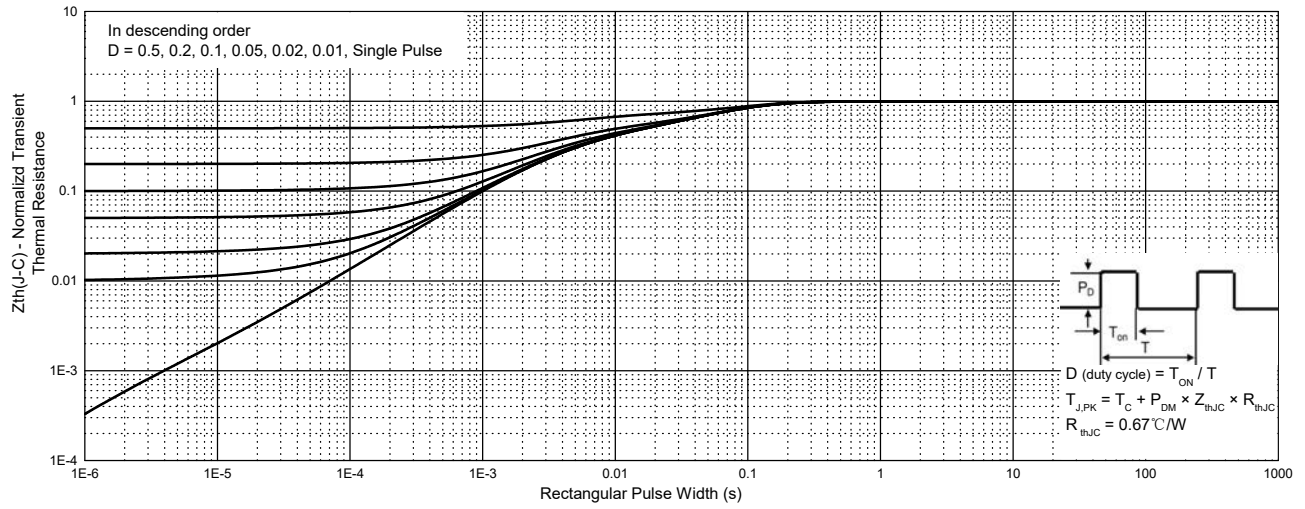


**Fig. 18 - Clamped Inductive Switching Energy vs. External Gate Resistor ( $R_{G(ext.)}$ )**



**Curve Characteristics** ( $T_J=25\text{ C}$  unless otherwise specified)

Fig.19 - Normalized Transient Thermal Impedance



## Ordering Information

Device	Packing
SICW080N120H-BP	Tube:30pcs/Tube, 1.8K/Ctn;

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